

SPECIFICATION

Device Name : IGBT-IPM

Type Name : 6MBP100NA060-01

Spec. No. : MS6M0277

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Fuji Electric Co.,Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED	Fuji Electric Co.,Ltd.		
DRAWN	Mar. 27 '96	H. Kawakami	T. HOSEN	DWG. NO.	MS6M0277	1 / 15
CHECKED	" "	N. Terasawa				

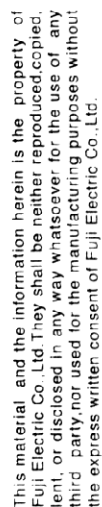
Revised Records

Date	Classi- fication	Ind.	Content	Applied date	Drawn	Checked	Approved
Mar. -27-'96	enactment	—	_____	Issued date	_____	N. Terasawa	T. HOSEN

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外形图

单位: mm



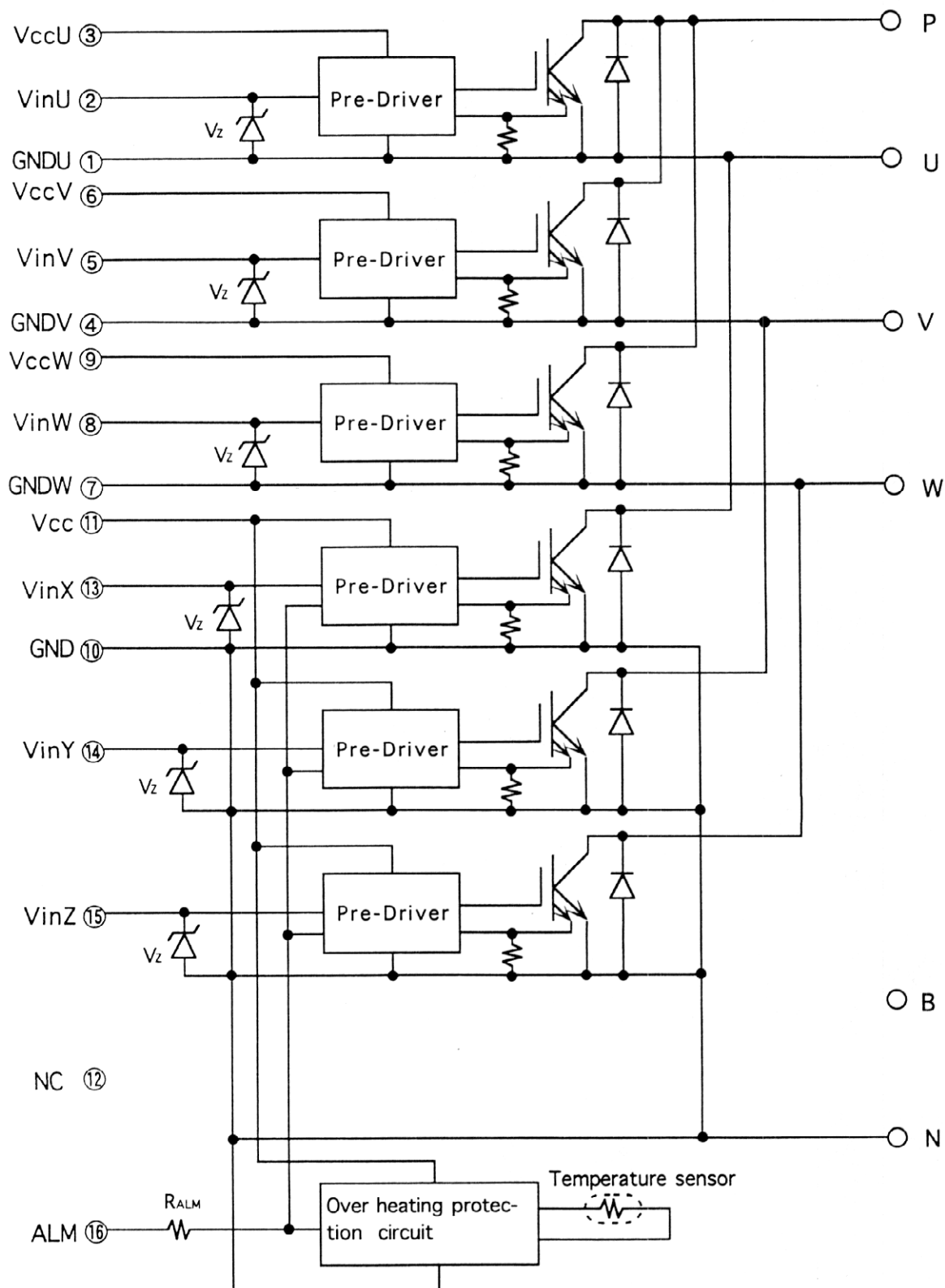
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H04-004-03

2 Block Diagram

ブロック図



Pre-Drivers include following functions

- ① Short Circuit Protection Circuit
- ② Amplifier for Driver
- ③ Under Voltage Lockout Circuit
- ④ Over current Protection Circuit

3. Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

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Items			Symbols	Ratings		Units
				Min.	Max.	
DC Bus Voltage			V _{DC}	0	450	V
DC Bus Voltage (surge)			V _{DC} (SURGE)	0	500	V
DC Bus Voltage (short operating)			V _{SC}	200	400	V
Collector-Emitter Voltage			V _{CES}	0	600	V
I N V	Collector Current	DC	I _c	—	100	A
		1mS	I _{cp}	—	200	A
		Duty=42.0%	-I _c	—	100	A
	Collector Power Dissipation	One Transistor	P _c	—	400	W
Junction Temperature			T _j		150	°C
Input Voltage of Power Supply for Pre-Driver			V _{CC} ※1	0	20	V
Input Signal Voltage			V _{in} ※2	0	V _z	V
Input Signal Current			I _{in}	—	1	mA
Alarm Signal Voltage			V _{ALM} ※3	0	V _{CC}	V
Alarm Signal Current			I _{ALM} ※4	—	15	mA
Storage Temperature			T _{stg}	-40	125	°C
Operating Case Temperature (Fig.1)			T _{OP}	-20	100	°C
Isolation Voltage (Case-Terminal)			V _{iso} ※5	—	AC2.5	kV

Note ※1 V_{CC} shall be applied to the input Voltage between terminal No. 3 and 1 , 6 and 4, 9 and 7, 11 and 10.

※2 V_{in} shall be applied to the input Voltage between terminal No. 2 and 1 , 5 and 4, 8 and 7, 12 13 14 15 and 10.

※3 V_{ALM} shall be applied to the Voltage between terminal No. 16 and 10.

※4 I_{ALM} shall be applied to the input current to terminal No. 16.

※5 50Hz/60Hz sine wave 1 minute.

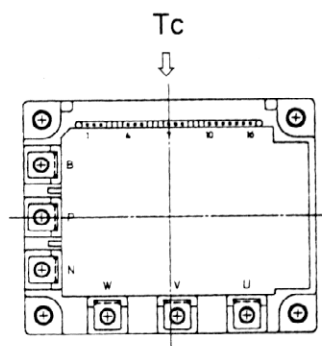


Fig.1 Measurement of case temperature

4. Electrical Characteristics

4.1 Electrical Characteristics of Power Circuit (at $T_c=T_j=25^{\circ}\text{C}$, $V_{cc}=15\text{V}$)

	Items	Symbols	Conditions	Min.	Typ.	Max.	Units
I N V	Collector Current at off Signal Input	I_{CES}	$V_{CE}=600\text{V}$	—	—	1.0	mA
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=100\text{A}$	—	—	2.9	V
	Forward Voltage of FWD	V_F	$-I_c=100\text{A}$	—	—	3.3	V

4.2 Electrical Characteristics of Control Circuit (at $T_c=T_j=25^{\circ}\text{C}$, $V_{cc}=15\text{V}$)

	Items	Symbols	Conditions	Min.	Typ.	Max.	Units
	Power Supply Current of P-Line Side Pre-Driver (One Unit)	I_{CCP}	$f_{sw}=15\text{kHz} \times 6$ Duty=50%	—	8	18	mA
	Power Supply Current of N-Line Side Three Pre-Drivers and Protection Circuits	I_{CCN}	$f_{sw}=15\text{kHz}$ Duty=50%	—	24	54	mA
	Input signal Threshold Voltage	$V_{in(ON)}$	ON	1.00	1.35	1.70	V
		$V_{in(OFF)}$	OFF	1.25	1.60	1.95	
	Zener Voltage	V_Z		6.9	—	7.7	V
	Over Heating Protection(OH) Level	T_{OH}	$V_{DC}=0\text{V}$, $I_c=0\text{A}$ Case Temperature	100	—	125	$^{\circ}\text{C}$
	OH Hysteresis	T_H		—	20	—	$^{\circ}\text{C}$
	Over Current Protection(OC) Level	I_{oc}	$T_j=125^{\circ}\text{C}$ Collector Current	130	—	—	A
	OC Delay Time (Fig.2)	t_{DOC}	$T_j=25^{\circ}\text{C}$	—	8	—	μS
	Under Voltage Protection(UV) Level	V_{UVT}		11.0	12.0	12.5	V
	UV Hysteresis	V_H		0.2	—	—	V
	Alarm Signal Hold Time	t_{ALM}		0.8	2	—	mS
	Delay Time of Short Circuit Protection (Fig.3)	t_{SC}		12	—	—	μS
	Limiting Resistor for Alarm	R_{ALM}		1425	1500	1575	Ω

※6 Switching frequency of IPM

4.3 Dynamic Characteristics (at $T_c=T_j=125^{\circ}\text{C}$, $V_{cc}=15\text{V}$)

	Items	Symbols	Conditions	Min.	Typ.	Max.	Units
Fig.4	Switching Time	t_{on}	$I_c=100\text{A}$	0.3	—	—	μS
		t_{off}	$V_{DC}=300\text{V}$	—	—	3.6	μS
	Switching Time (FWD)	t_{rr}	$I_F=100\text{A}$, $V_{DC}=300\text{V}$	—	—	400	nS

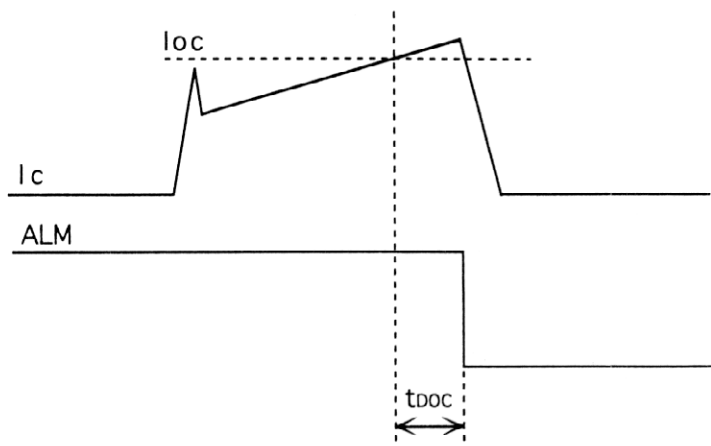


Fig.2 : Definition of OC Delay Time

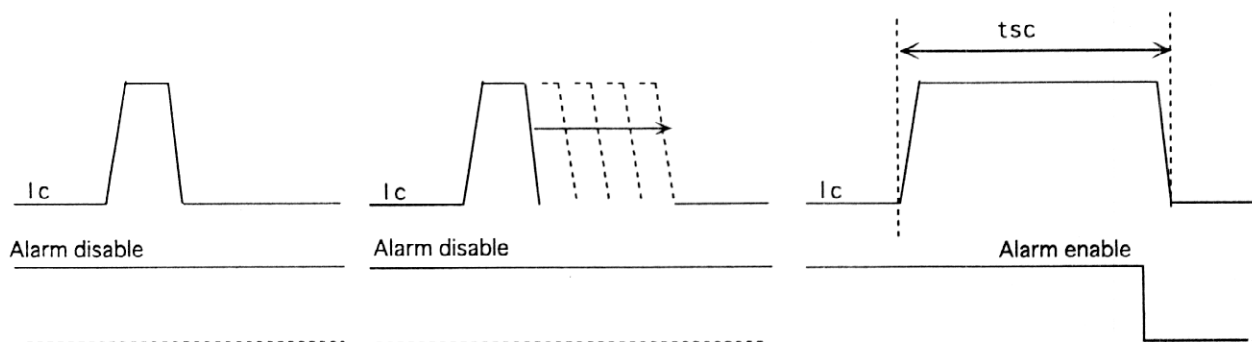


Fig.3 : Definition of tsc

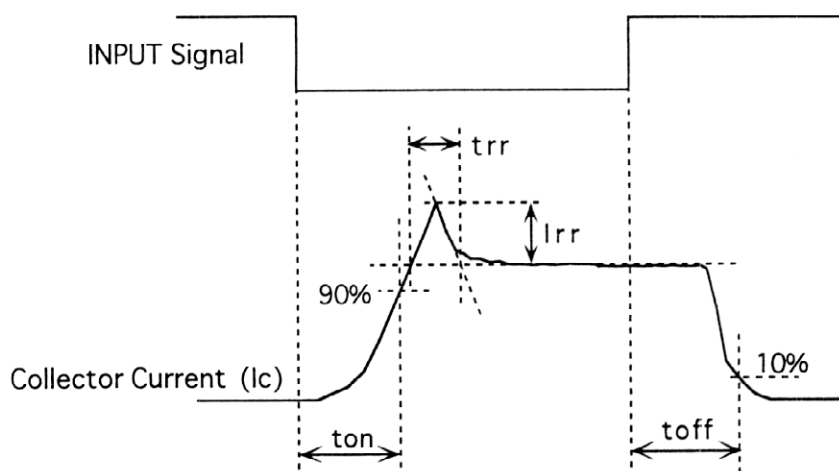


Fig.4 : Definition of switching time

5. Thermal Characteristics (Tc=25℃)

Items			Symbols	Min.	Typ.	Max.	Units
Junction to Case Thermal Resistance	INV	IGBT	Rth(j-c)	—	—	0.31	℃/W
		FWD	Rth(j-c)	—	—	0.90	℃/W
Case to Fin Thermal Resistance with Compound			Rth(c-f)	—	0.05	—	℃/W

6.Mechanical Characteristics

Items		Min.	Typ.	Max.	Units
Screw Torque	Mounting (M5)	—	—	3.5	N·m
	Terminal (M5)	—	—	3.5	N·m
Weight		—	550	—	g

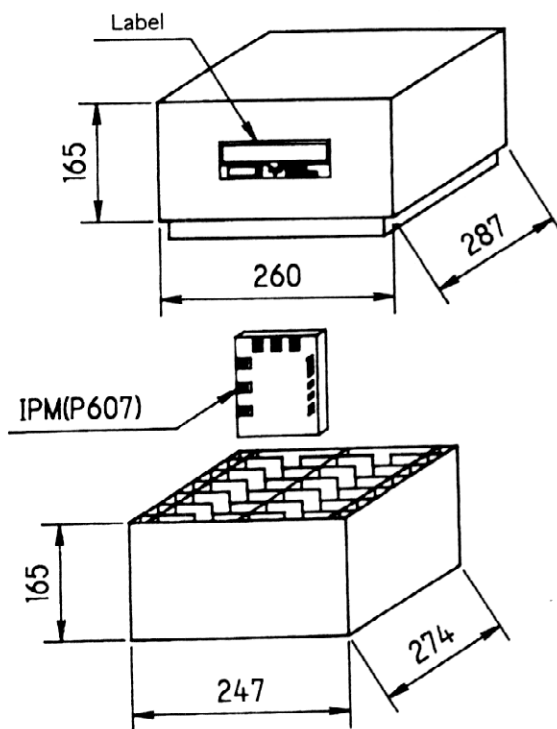
7.Recommendable Value

Items		Symbols	Conditions	Min.	Typ.	Max.	Units
DC Bus Voltage		Vdc		200	—	400	V
Operating Power Supply Voltage Range of Pre-Driver		Vcc		13.5	15	16.5	V
Switching frequency of IPM		fsw		1	—	20	kHz
Screw Torque	Mounting (M5)	—		2.5	—	3.5	N·m
	Terminal (M5)	—		2.5	—	3.5	N·m

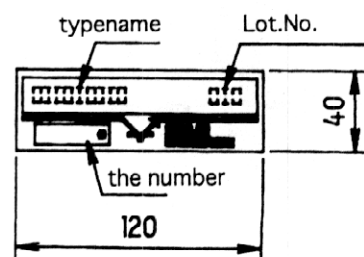
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8. Packing and labeling

梱包箱と表示



material card board
weight 5.5 kg (Max.)
products 10pcs (Max.)



9. Storage and transportation notes (保管、運搬上の注意事項)

- The IGBT-IPM should be stored at a standard temperature of 5 to 35 °C and humidity of 45 to 75%.

常温保存が望ましい。(5~35℃、45~75%)

- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.

急激な温度変化の無きこと。(モジュール表面が結露しないこと)

- Avoid exposure to corrosive gases and dust.

腐食性ガスの発生場所、塵埃の多い場所は避けること。

- Avoid excessive external force on the module.

製品に荷重がかからないように十分に注意すること。

- Store modules with unprocessed terminals.

モジュールの端子は未加工の状態での保管すること。

- Do not drop or otherwise shock the modules when transporting.

製品の運搬時に衝撃を与えたり、落下させたりしないこと。

10. Applicable category (適用範囲)

This specification is applied to IGBT-IPM named 6MBP100NA060-01.

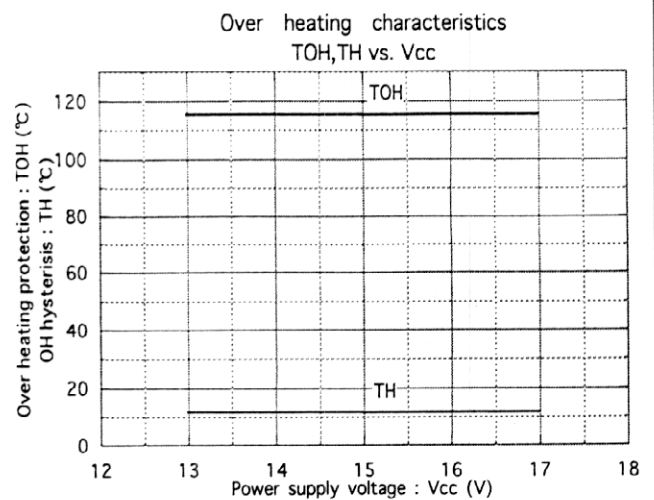
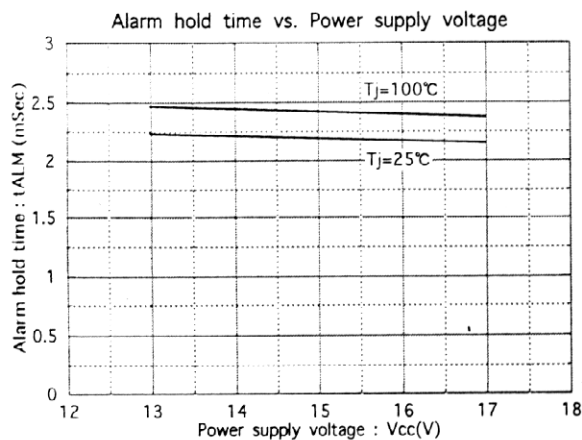
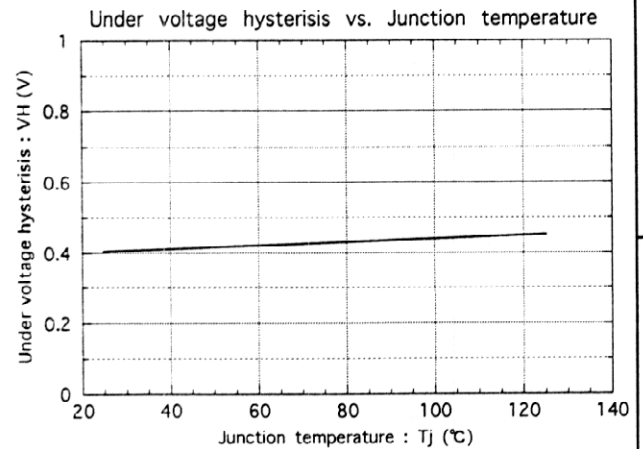
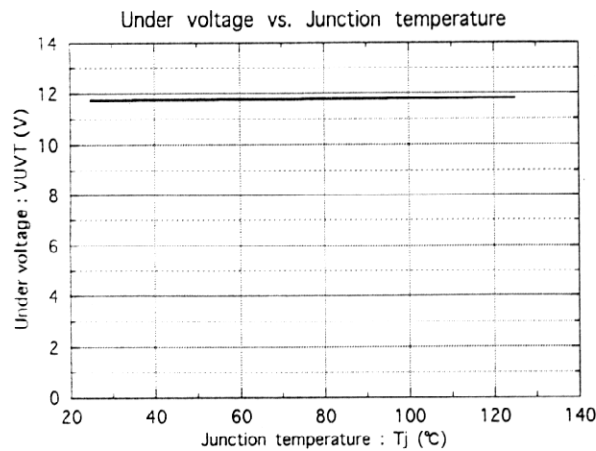
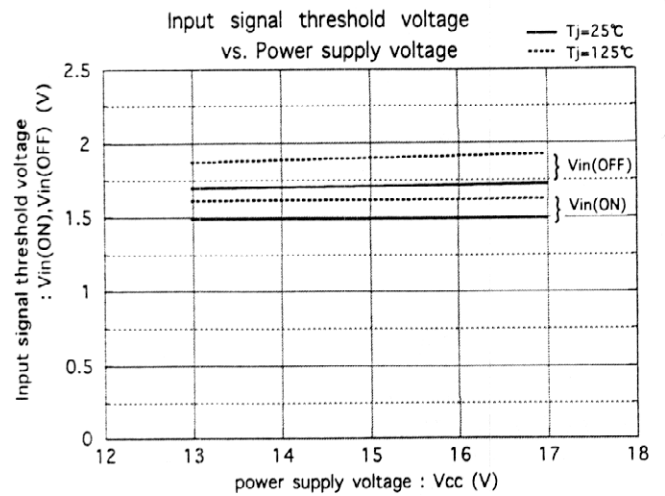
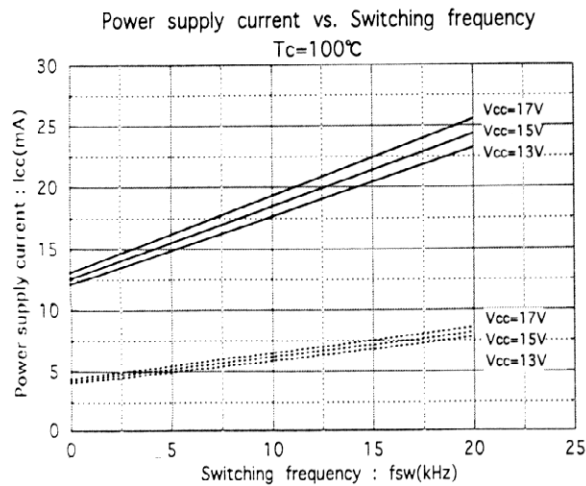
本納入仕様書は、IGBT-IPM 6MBP100NA060-01 に適用する。

11. Characteristic (Representative)

特性カーブ（代表例）

11-1. Control Circuit

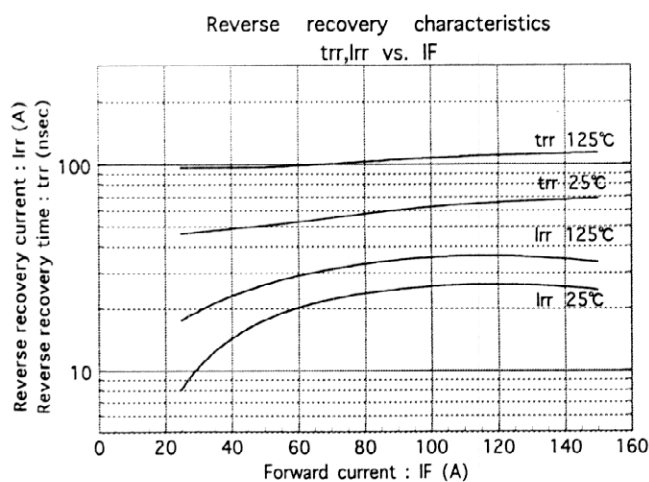
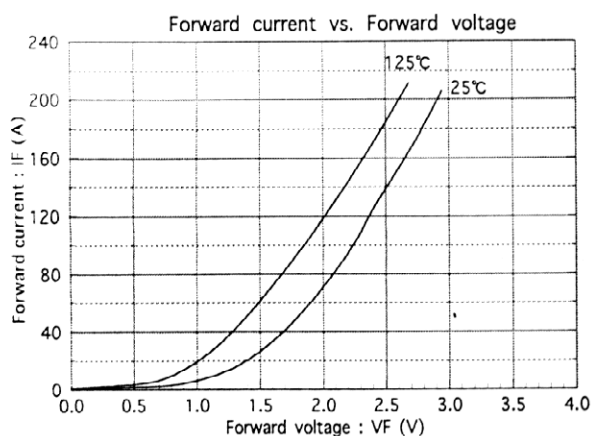
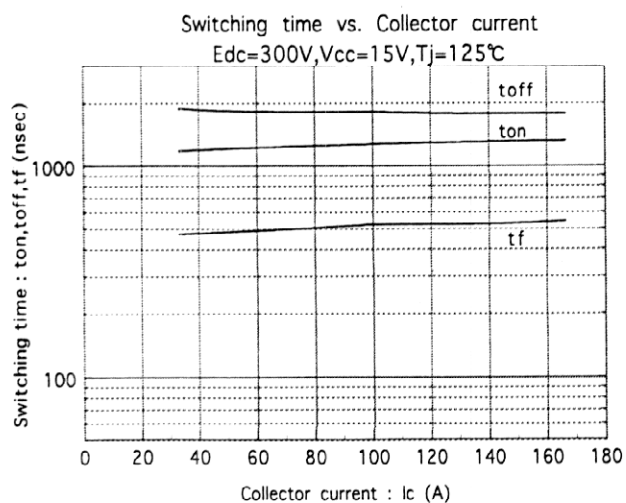
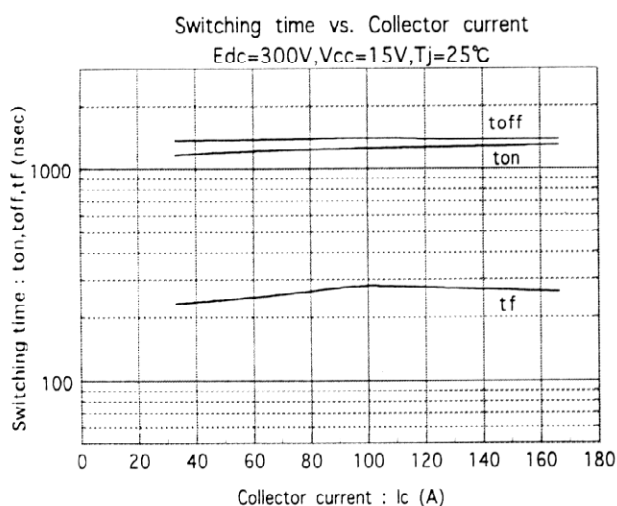
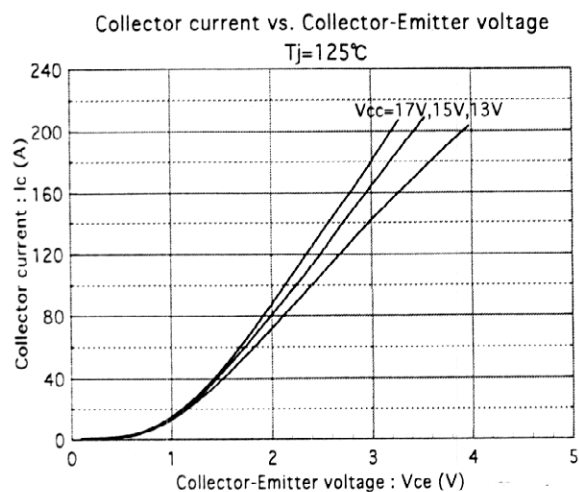
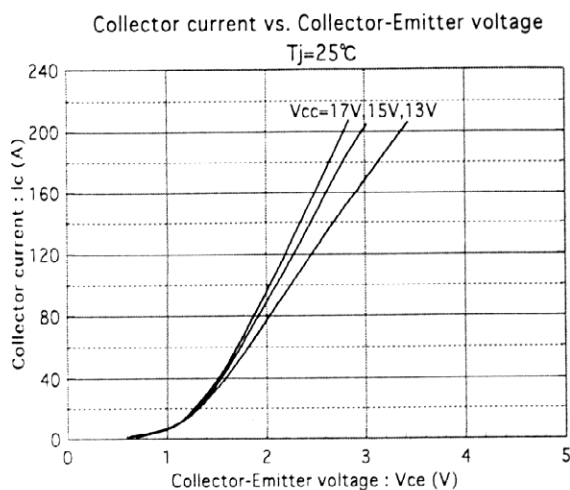
制御部



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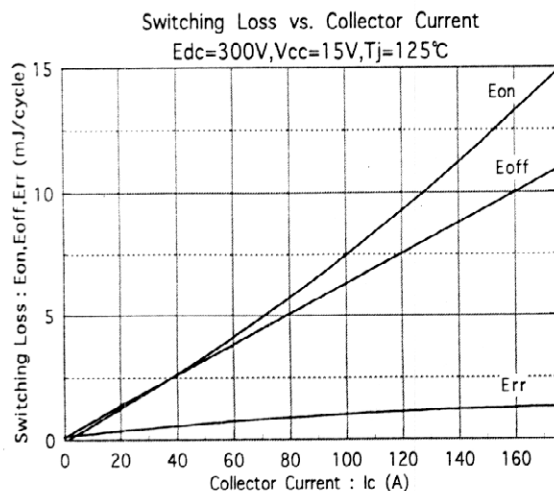
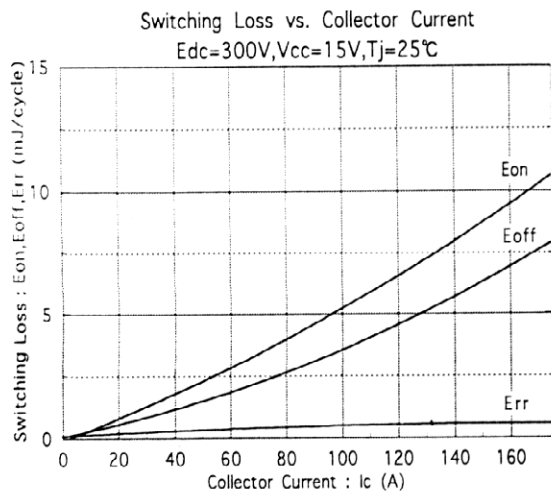
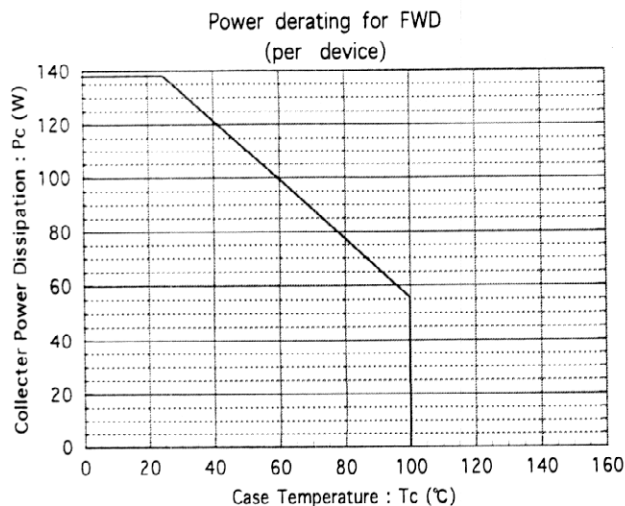
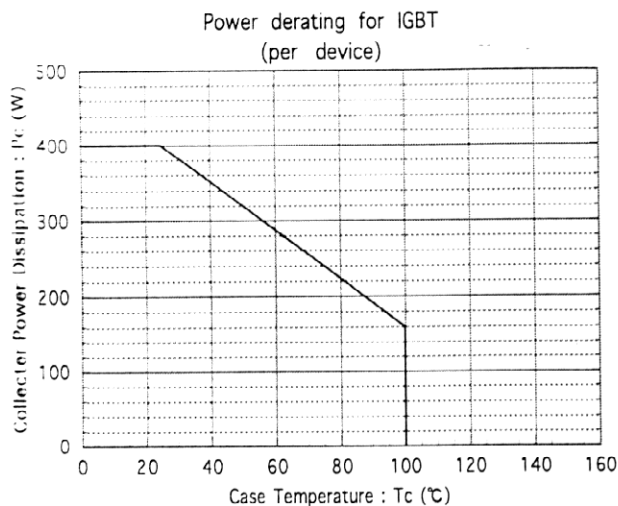
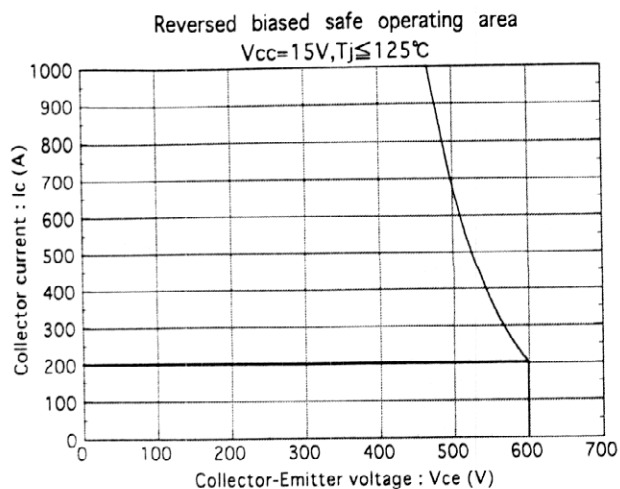
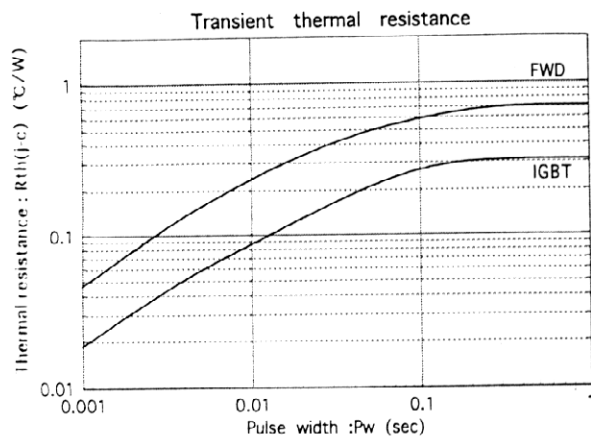
11-2. Inverter

インバータ部

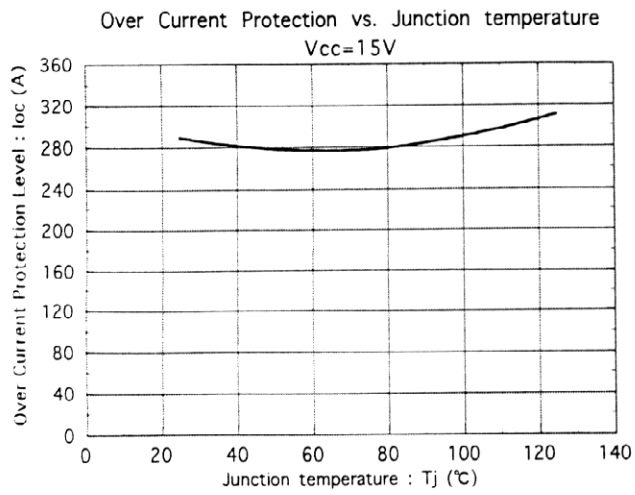


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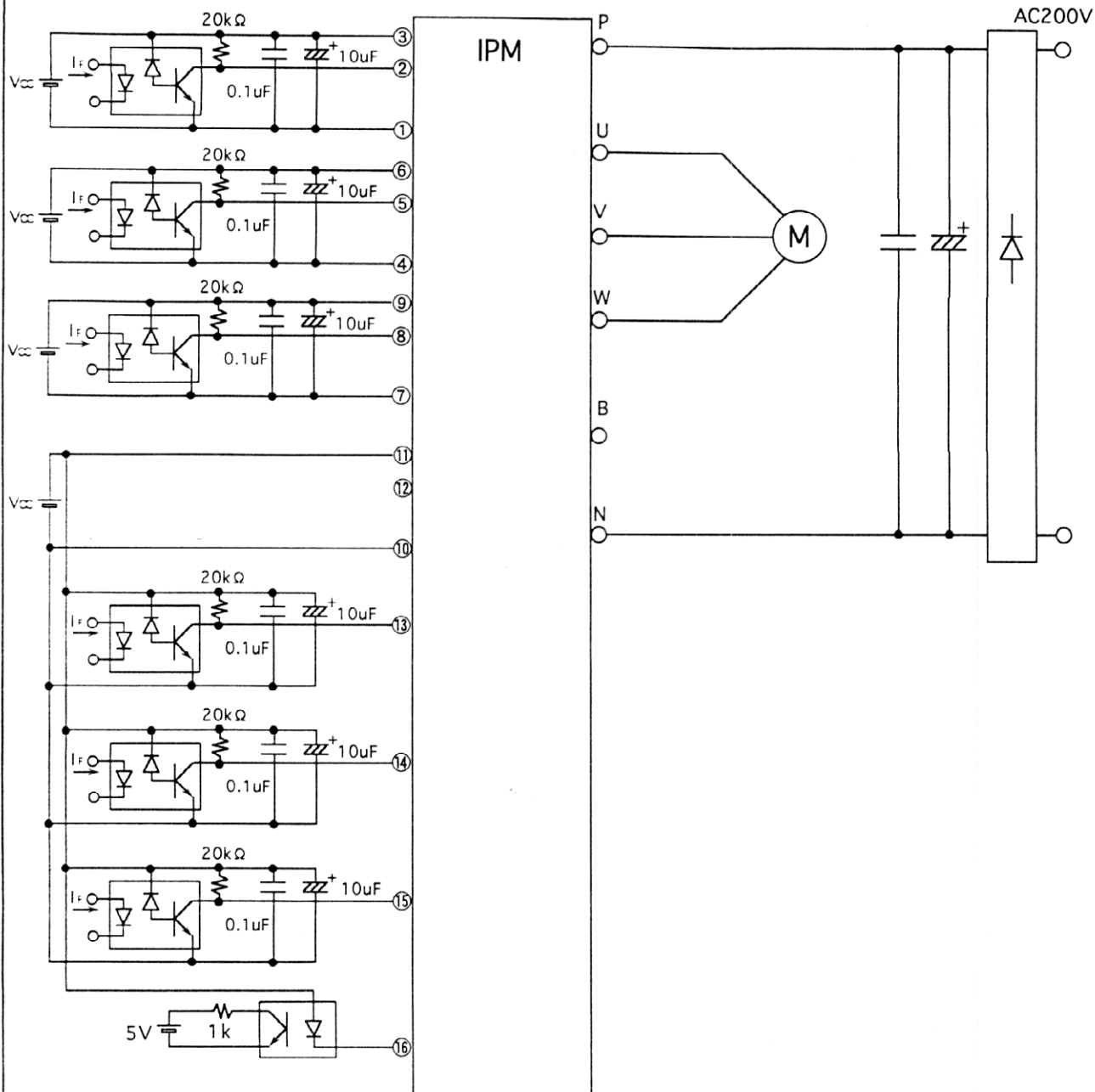
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12.Example of applied circuit (応用回路例)



- The wiring between opto-coupler and input terminal of IPM should be shorter as much as possible.
The stray-capacitance between primary and secondary side of opto-coupler should not be increased by pattern lay-out.
ホトカブラとIPMの入力端子間配線は、できるだけ短くしホトカブラの1次・2次間の浮遊容量を増加させないパターンレイアウトとして下さい。
- Capacitor should be installed to VCC-GND terminal of high-speed opto-coupler closely as much as possible.
高速ホトカブラのVcc-GND間には、コンデンサをできるだけ近接して取り付けして下さい。
- Use high-speed opto-coupler : $t_{PLH}, t_{PHL} \leq 0.8\mu s$, high CMR type. (Example : HCPL-4504)
高速ホトカブラ : $t_{PLH}, t_{PHL} \leq 0.8\mu s$, 高CMRタイプをご使用下さい。(例 HPCL-4504)
- Low-speed opto-coupler : $CTR \geq 100\%$
低速ホトカブラ : $CTR \geq 100\%$

- Each power supply for drive circuit should not have transient voltage fluctuation. Four power supplies which are isolated should be supplied individually.
各制御用電源は瞬時電圧変動の少ない、絶縁したものを4個独立にして供給して下さい。
- The DC bus line to the P-N terminal should have lower inductance as much as possible, such as connecting capacitor to P-N terminal, in order to reduce surge voltage.
P-N間の直流母線はできるだけ低インダクタンス化し、P-N端子間にコンデンサを接続するなどしてサージ電圧を低減して下さい。
- In order to avoid noise from AC line, connect capacitor (about 4.7uF) between three-phase line and earth.
ACラインからのノイズ侵入を防ぐため、三相各線-大地間に4.7nF程度のコンデンサを接続して下さい。
- Do not connect N-terminal of main circuit to ground (GND) of input circuit.
入力回路のグラウンド (GND) と主回路 N 端子を IPM の外側で接続しないで下さい。
- In case of using connector for connection to control terminal, it must be Au-plated electrode and 2.54mm of pitch.
制御端子との接続にコネクタを用いる場合は、金メッキ電極・2.54mm ピッチのものをご使用下さい。
- When capacitor is connected between input and GND terminal, pay attention to longer delay time after signal inputted to primary side of opto-coupler.
入力端子-GND間にコンデンサを接続するとホトカプラ1次側入力信号に対する応答時間が長くなりますのでご注意下さい。